Title (en)

IMPROVED FAR-FIELD NITRIDE BASED SEMICONDUCTOR LASER

Title (de)

NITRID - HALBLEITERLASER MIT VERBESSERTEM FERNFELD

Title (fr)

LASER AMELIORE A SEMI-CONDUCTEUR AU NITRURE A CHAMP LOINTAIN

Publication

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Application

EP 99954948 A 19991014

Priority

- JP 31399398 A 19981016
- US 9924146 W 19991014

Abstract (en)

[origin: WO0024097A1] A nitride semiconductor device that comprises a first layer, a second layer and a buffer layer sandwiched between the first layer and the second layer. The second layer is a layer of a single-crystal nitride semiconductor material including AIN and has a thickness greater than the thickness at which cracks would form if the second layer was grown directly on the first layer. The buffer layer is a layer of a low-temperature-deposited nitride semiconductor material that includes AIN. Incorporating the nitride semiconductor device into a semiconductor laser diode enables the laser diode to generate coherent light having a far-field pattern that exhibits a single peak.

IPC 1-7

H01S 5/20

IPC 8 full level

H01S 5/00 (2006.01); **H01S 5/20** (2006.01); **H01S 5/323** (2006.01); **H01S 5/343** (2006.01)

CPC (source: EP)

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See references of WO 0024097A1

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